

1.1 Scope.

This specification covers the detail requirements for a monolithic CMOS 16×16-bit digital multiplier integrated circuit.

1.2 Part Number.

The complete part number per Table 1 of this specification is as follows:

Device	Part Number ¹
–1	ADSP-1016AS(X)/883B
–2	ADSP-1016AT(X)/883B

NOTE

¹See paragraph 1.2.3 for package identifier.

1.2.3 Case Outline.

See Appendix 1 of General Specification ADI-M-1000: package outline:

(X)	Package	Description
D	D-64A	64-Pin DIP
E	E-68A	68-Contact LCC
G	G-68A	68-Lead Pin Grid Array

1.3 Absolute Maximum Ratings.

Supply Voltage	–0.3 V to 7 V
Input Voltage	–0.3 V to V_{DD}
Output Voltage	–0.3 V to V_{DD}
Operating Temperature Range (Ambient)	–55°C to +125°C
Storage Temperature Range	–65°C to +150°C
Lead Temperature (Soldering 10 sec)	+300°C

1.5 Thermal Characteristics.

Thermal Resistance θ_{JC} : see MIL-M-38510, Appendix C.

ADSP-1016A – SPECIFICATIONS

Parameter	Symbol	Device	Design Limit @ +25°C	Sub Group 1	Sub Group 2, 3	Sub Group 9	Sub Group 10, 11	Test Condition ¹	Units
Digital Input High Voltage	V _{IH}	-1, 2	2.0	2.0	2.0			V _{DD} = max	V min
Digital Input Low Voltage	V _{IL}	-1, 2	0.8	0.8	0.8			V _{DD} = min	V max
Digital Output High Voltage	V _{OH}	-1, 2	2.4	2.4	2.4			V _{DD} = min I _{OH} = -0.4 mA	V min
Digital Output Low Voltage*	V _{OL}	-1, 2	0.4	0.6	0.6			V _{DD} = min I _{OL} = +4 mA	V max
Digital Input High Current	I _{IH}	-1, 2	10	10	10			V _{DD} = max V _{IN} = +5.0 V	μA max
Digital Input Low Current	I _{IL}	-1, 2	10	10	10			V _{DD} = max V _{IN} = 0.0 V	μA max
Three-State Leakage Current Low	I _{OZL}	-1, 2	50	50	50			V _{DD} = max V _{IL} = 0 V (High Z)	μA max
Three-State Leakage Current High	I _{OZH}	-1, 2	50	50	50			V _{DD} = max V _{IH} = max (High Z)	μA max
Supply Current*	I _{DD1}	-1, 2	45	55	55			V _{DD} = max; TTL Inputs; f = max	mA max
	I _{DD2}	-1, 2	35	40	40			V _{DD} = max All V _{IN} = 2.4 V	mA max
Output Delay*	t _D	-1, 2	20			35	35 ³	Note 2	ns max
Three-State Enable* (High Z to Low)	t _{ENA}	-1, 2	20			35	35	Notes 2 and 3	ns max
Three-State Disable* (Low to High Z)	t _{DIS}	-1, 2	20			35	35	Notes 2 and 3	ns max
Clock Pulse Width	t _{PW}	-1, 2	15			15	15	Note 2	ns min
Input Data Setup Time*	t _{DS}	-1, 2	25			25	25	Note 2	ns min
Input Control Setup Time*	t _{CS}	-1, 2	30			30	30	Notes 2 and 3	ns min
Input Hold Time	t _H	-1, 2	2			2	2	Note 2	ns min
Unclocked Multiply Time*	t _{MUC}	-1	105			120	120	Note 2	ns max
		-2	90			105	105		
Clocked Multiply Time*	t _{MC}	-1	85			95	95	Note 2	ns max
		-2	70			80	80		

NOTES

*Indicates that a limit for this parameter has changed from REV. D.

¹T_A = +25°C; V_{DD} = +4.5 V min to +5.5 V max (unless otherwise noted).

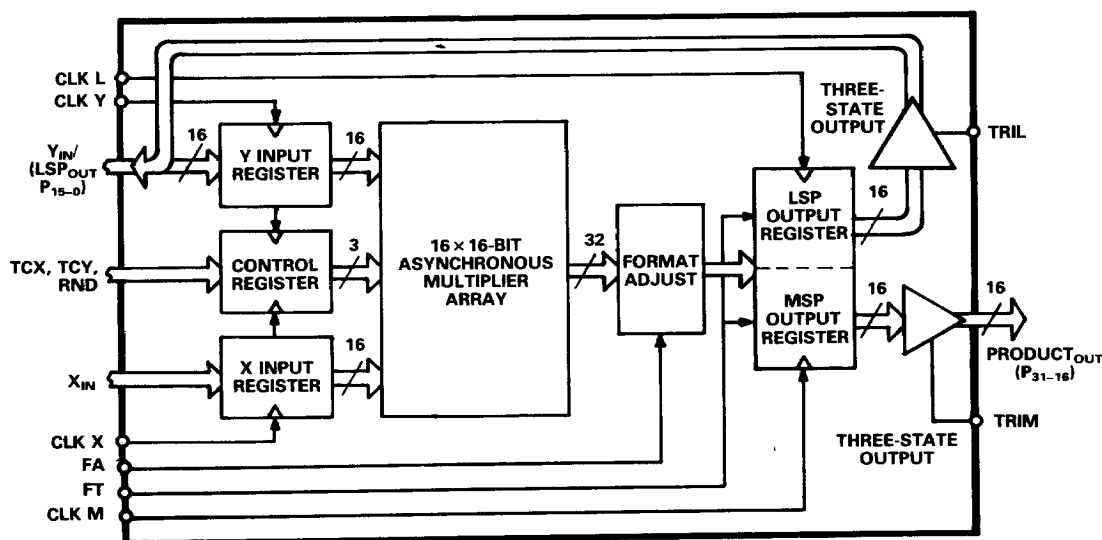
²TTL inputs of 0 V and +3.0 V; V_{DD} = +4.5 V, rise time = 5 ns, and timing transitions, per Figure 1, measured at +1.5 V (unless otherwise noted).

³Transitions measured per Figure 2.

Table 1.

REV. E

3.2.1 Functional Block Diagram and Terminal Assignments.



Functional Block Diagram

Pin Assignments

PIN NO.	FUNCTION			PIN NO.	FUNCTION		
	DIP	LCC	PIN-GRID		DIP	LCC	PIN-GRID
1	X4	X4	P0, Y0	35	P26	P24	CLK M
2	X3	X3	P1, Y1	36	P27	P25	TRIM
3	X2	X2	P2, Y2	37	P28	P26	FA
4	X1	X1	P3, Y3	38	P29	P27	FT
5	X0	X0	P4, Y4	39	P30	P28	GND
6	TRIL	TRIL	P5, Y5	40	P31	P29	GND
7	CLK L	CLK L	P6, Y6	41	CLK M	P30	GND
8	CLK Y	CLK Y	P7, Y7	42	TRIM	P31	V _{DD}
9	P0, Y0	N/C	P8, Y8	43	FA	N/C	V _{DD}
10	P1, Y1	P0, Y0	P9, Y9	44	FT	CLK M	TCY
11	P2, Y2	P1, Y1	P10, Y10	45	GND	TRIM	TCX
12	P3, Y3	P2, Y2	P11, Y11	46	GND	FA	RND
13	P4, Y4	P3, Y3	P12, Y12	47	GND	FT	CLK X
14	P5, Y5	P4, Y4	P13, Y13	48	V _{DD}	GND	X15
15	P6, Y6	P5, Y5	P14, Y14	49	V _{DD}	GND	X14
16	P7, Y7	P6, Y6	P15, Y15	50	TCY	GND	X13
17	P8, Y8	P7, Y7	N/C	51	TCX	V _{DD}	N/C
18	P9, Y9	P8, Y8	P16	52	RND	V _{DD}	X12
19	P10, Y10	P9, Y9	P17	53	CLK X	TCY	X11
20	P11, Y11	P10, Y10	P18	54	X15	TCX	X10
21	P12, Y12	P11, Y11	P19	55	X14	RND	X9
22	P13, Y13	P12, Y12	P20	56	X13	CLK X	X8
23	P14, Y14	P13, Y13	P21	57	X12	X15	X7
24	P15, Y15	P14, Y14	P22	58	X11	X14	X6
25	P16	P15, Y15	P23	59	X10	X13	X5
26	P17	N/C	P24	60	X9	N/C	X4
27	P18	P16	P25	61	X8	X12	X3
28	P19	P17	P26	62	X7	X11	X2
29	P20	P18	P27	63	X6	X10	X1
30	P21	P19	P28	64	X5	X9	X0
31	P22	P20	P29	65	N/A	X8	TRIL
32	P23	P21	P30	66	N/A	X7	CLK L
33	P24	P22	P31	67	N/A	X6	CLK Y
34	P25	P23	N/C	68	N/A	X5	N/C

3.2.4 Microcircuit Technology Group.

This microcircuit is covered by technology group (105).

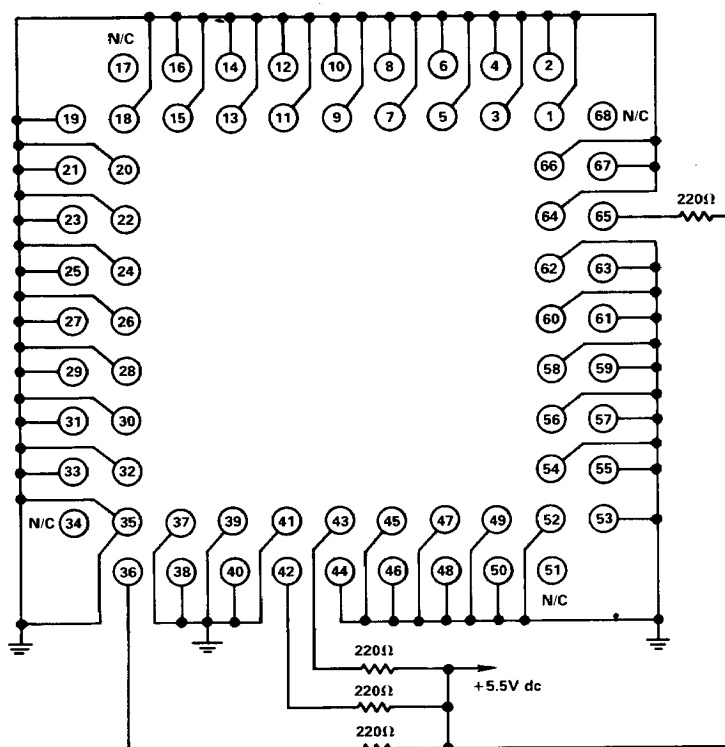
REV. E

733

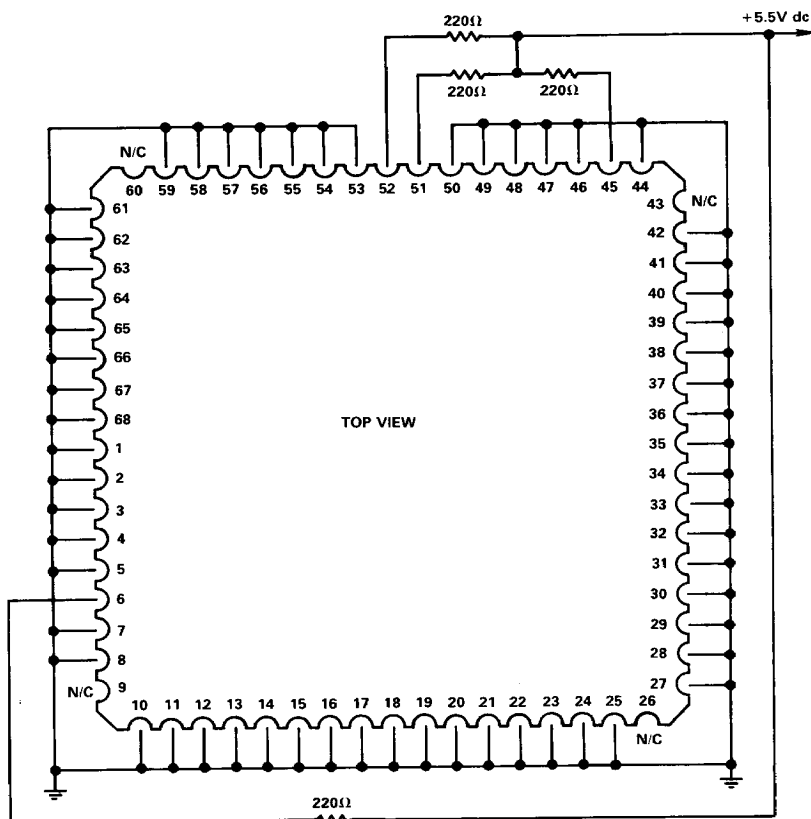
ADSP-1016A

4.2.1 Life Test/Burn-In Circuit.

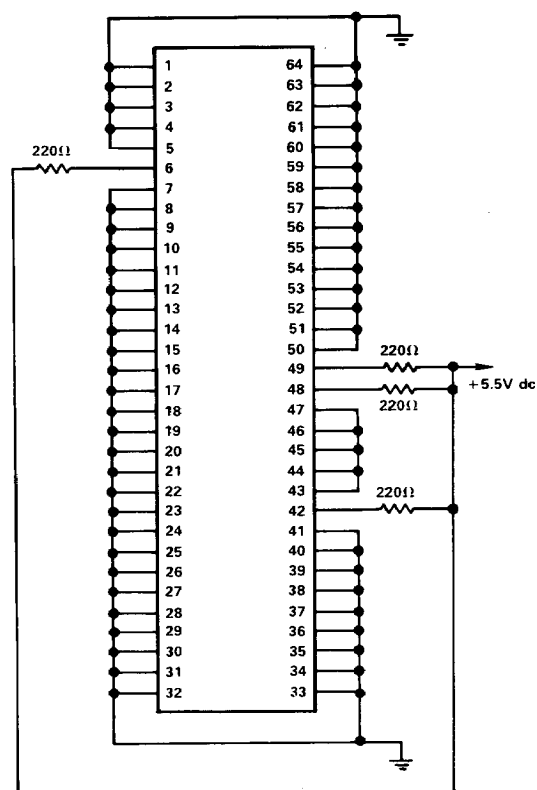
Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).



ADSP-1016AG Life Test and Burn-In Circuit



ADSP-1016AE Life Test and Burn-In Circuit



ADSP-1016AD Life Test and Burn-In Circuit

REV. E

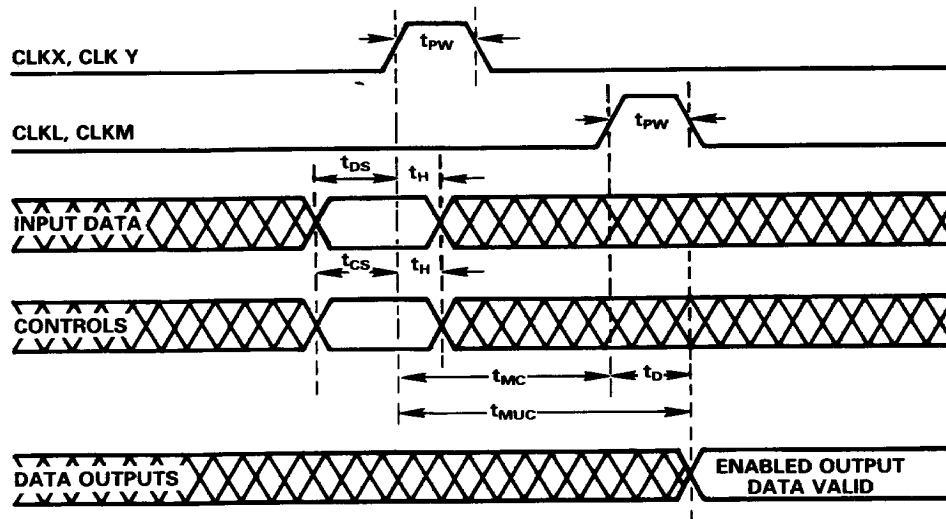


Figure 1. ADSP-1016A Timing Diagram

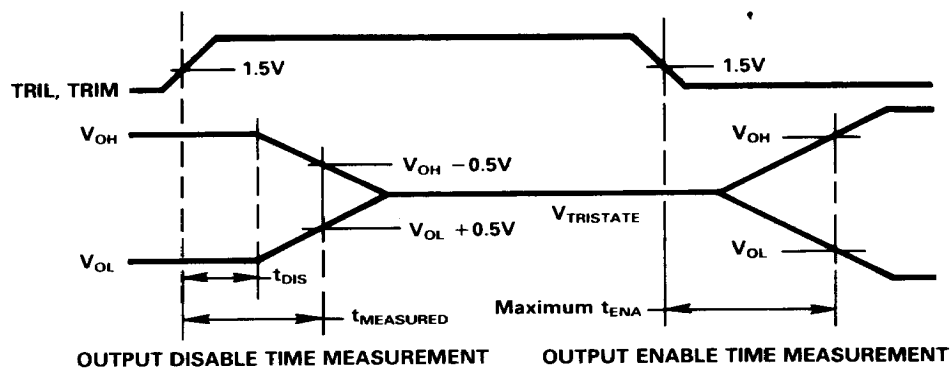


Figure 2. Three-State Disable and Enable Timing

Output disable time, t_{DIS} , is measured from the time the output enable control signal reaches 1.5 V to the time when all outputs have ceased driving. This is calculated by measuring the time, $t_{MEASURED}$, from the same starting point to when the output voltages have changed by 0.5 V toward +1.5 V. From the tester capacitive loading, C_L , and the measured current, i_L , the decay time, t_{DECAY} , can be approximated to first order by:

$$t_{DECAY} = \frac{C_L \cdot 0.5 \text{ V}}{i_L}$$

from which

$$t_{DIS} = t_{MEASURED} - t_{DECAY}$$

is calculated. Disable times are longest at the highest specified temperature.

The maximum output enable time, maximum t_{ENA} , is also measured from output enable control signal at 1.5 V to the time when all outputs have reached TTL input levels (V_{OH} or V_{OL}). This could also be considered as "data valid." Maximum enable times are longest at the highest specified temperature.

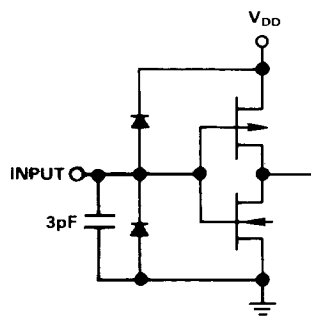


Figure 3. Equivalent Input Circuit

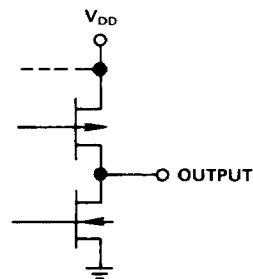


Figure 4. Equivalent Output Circuit

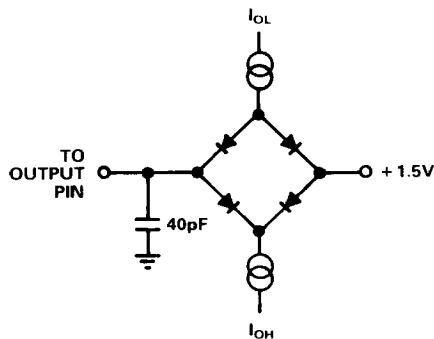


Figure 5. Normal Load Circuit for AC Measurements